

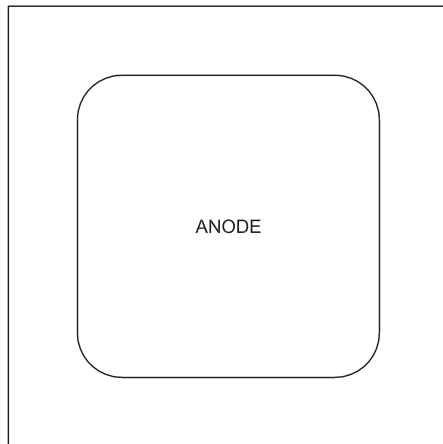
**PROCESS CPD24**  
**Fast Recovery Rectifier**  
1 Amp Glass Passivated Rectifier Chip



**PROCESS DETAILS**

|                        |                       |
|------------------------|-----------------------|
| Process                | GLASS PASSIVATED MESA |
| Die Size               | 51 x 51 MILS          |
| Die Thickness          | 11 MILS               |
| Anode Bonding Pad Area | 35 x 35 MILS          |
| Top Side Metalization  | Ni/Au - 5,000Å/2,000Å |
| Back Side Metalization | Ni/Au - 5,000Å/2,000Å |

**GEOMETRY**



BACKSIDE CATHODE R1

**GROSS DIE PER 4 INCH WAFER**

4,250

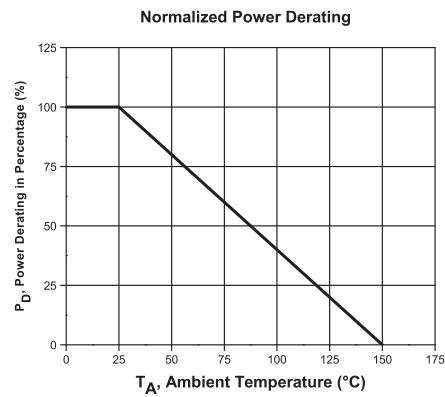
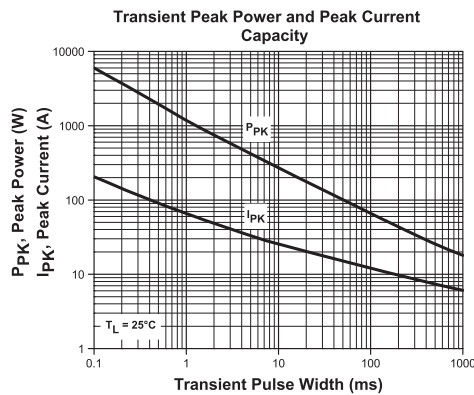
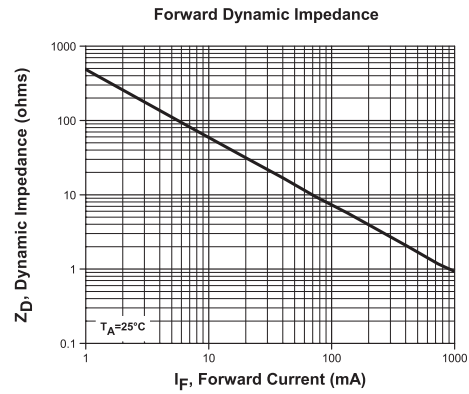
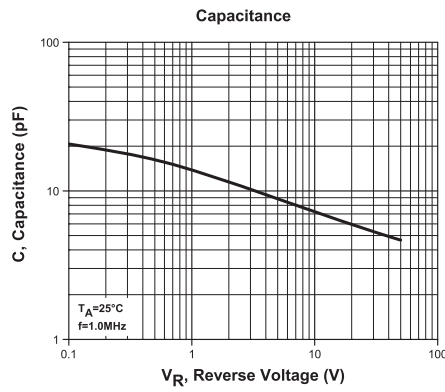
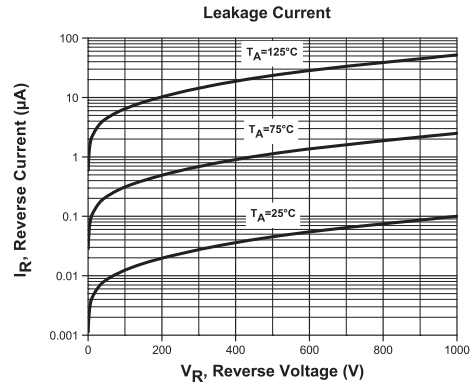
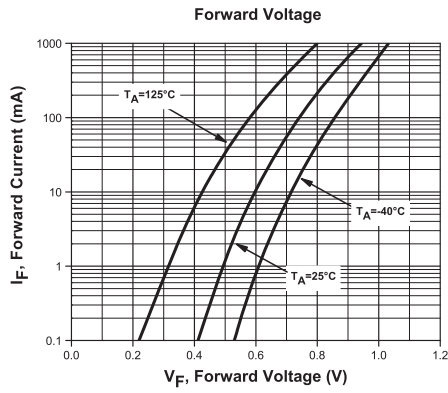
**PRINCIPAL DEVICE TYPES**

1N4933 thru 1N4937  
1N4942 thru 1N4948  
1N5615 thru 1N5623  
CMR1F-02M Series

R3 (29-April 2010)

# PROCESS CPD24

## Typical Electrical Characteristics



R3 (29-April 2010)